

256 Mbit Consumer FCRAM™

1.8 V, ×64, Low Power SDR SDRAM, SiP-oriented

MB81ES256445

■ FEATURES

- RAM featuring low power consumption and high-speed data transfer
- Low Power SDR SDRAM interface
- 1M-word × 64bit × 4-bank organization
- 1.8V Power Supply ($V_{DD}=V_{DDQ}$)
- Junction Temperature $T_J = -10^{\circ}\text{C}$ to $+105^{\circ}\text{C}$
- Auto precharge option for each burst access
- Configurable Driver Strength and Pre Driver Strength
- Auto Refresh and Self Refresh Modes
- Deep Power Down Mode

■ MAIN SPECIFICATIONS

Part Number	MB81ES256445
Organization	1 M Word × 64 bit × 4-bank
Interface	Low Power SDR
Supply Voltage	1.7 V to 1.95 V
Burst Operating Frequency (Max.)	166 MHz
CLK Access Time (Min.)	6 ns
Active Current (Max.)	75 mA
Deep Power Down Current (Max.)	20 μA

Note: FCRAM is a trademark of FUJITSU MICROELECTRONICS LIMITED, Japan.